



PJP10N60 / PJF10N60

600V N-Channel Enhancement Mode MOSFET

TO-220AB / ITO-220AB

FEATURES

- 10A , 600V, $R_{DS(ON)}=1.0\Omega@V_{GS}=10V, I_D=5.0A$
- Low ON Resistance
- Fast Switching
- Low Gate Charge
- Fully Characterized Avalanche Voltage and Current
- Specially Designed for AC Adapter, Battery Charge and SMPS
- In compliance with EU RoHs 2002/95/EC Directives

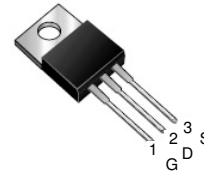
MECHANICAL DATA

- Case: TO-220AB / ITO-220AB Molded Plastic
- Terminals : Solderable per MIL-STD-750,Method 2026

ORDERING INFORMATION

TYPE	MARKING	PACKAGE	PACKING
PJP10N60	P10N60	TO-220AB	50PCS/TUBE
PJF10N60	F10N60	ITO-220AB	50PCS/TUBE

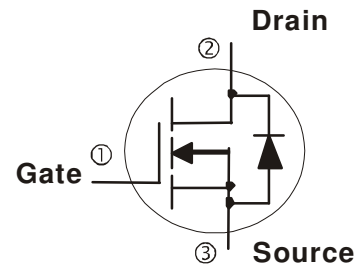
TO-220AB



ITO-220AB



INTERNAL SCHEMATIC DIAGRAM



Maximum RATINGS and Thermal Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	Symbol	PJP10N60	PJF10N60	Units
Drain-Source Voltage	V_{DS}	600		V
Gate-Source Voltage	V_{GS}	± 30		V
Continuous Drain Current	I_D	10	10	A
Pulsed Drain Current ¹⁾	I_{DM}	40	40	A
Maximum Power Dissipation Derating Factor	P_D	156 1.25	50 0.4	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150		$^\circ\text{C}$
Avalanche Energy with Single Pulse $I_{AS}=10A, V_{DD}=50V, L=10mH$	E_{AS}	500		mJ
Junction-to-Case Thermal Resistance	$R_{\theta JC}$	0.8	2.5	$^\circ\text{C/W}$
Junction-to Ambient Thermal Resistance	$R_{\theta JA}$	62.5	100	$^\circ\text{C/W}$

Note: 1. Maximum DC current limited by the package

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ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Units
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	600	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.0	-	4.0	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =5.0A	-	0.78	1.0	Ω
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =600V, V _{GS} =0V	-	-	10	μA
Gate Body Leakage	I _{GSS}	V _{GS} =±30V, V _{DS} =0V	-	-	±100	nA
Dynamic						
Total Gate Charge	Q _g	V _{DS} =480V, I _D =10A, V _{GS} =10V	-	41.6	52	nC
Gate-Source Charge	Q _{gs}		-	8.6	-	
Gate-Drain Charge	Q _{gd}		-	14.2	-	
Turn-On Delay Time	t _{d(on)}	V _{DD} =300V, I _D =10A V _{GS} =10V, R _G =25Ω	-	16.2	22	ns
Turn-On Rise Time	t _r		-	18.6	32	
Turn-Off Delay Time	t _{d(off)}		-	40.2	86	
Turn-Off Fall Time	t _f		-	22.8	38	
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V f=1.0MHz	-	1520	-	pF
Output Capacitance	C _{oss}		-	140	-	
Reverse Transfer Capacitance	C _{rss}		-	12.5	-	
Source-Drain Diode						
Max. Diode Forward Current	I _S	-	-	-	10	A
Max.Pulsed Source Current	I _{SM}	-	-	-	40	A
Diode Forward Voltage	V _{SD}	I _S =10A, V _{GS} =0V	-	-	1.4	V
Reverse Recovery Time	t _{rr}	V _{GS} =0V, I _F =10A di/dt=100A/us	-	420	-	ns
Reverse Recovery Charge	Q _{rr}		-	4.2	-	μC

NOTE: Plus Test : Pluse Width ≤ 300us, Duty Cycle ≤ 2%.



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Typical Characteristics Curves ($T_a=25^\circ\text{C}$, unless otherwise noted)

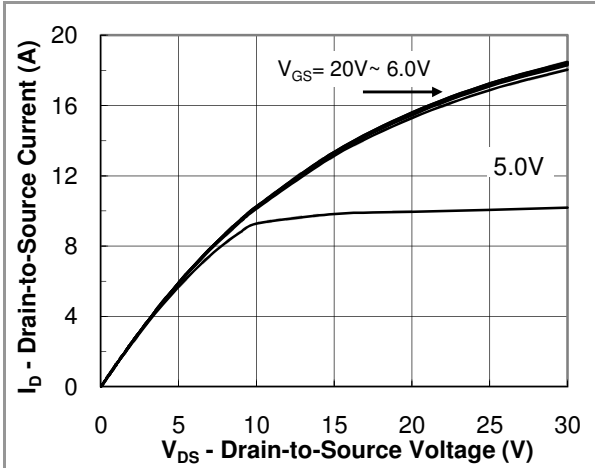


Fig.1 Output Characteristic

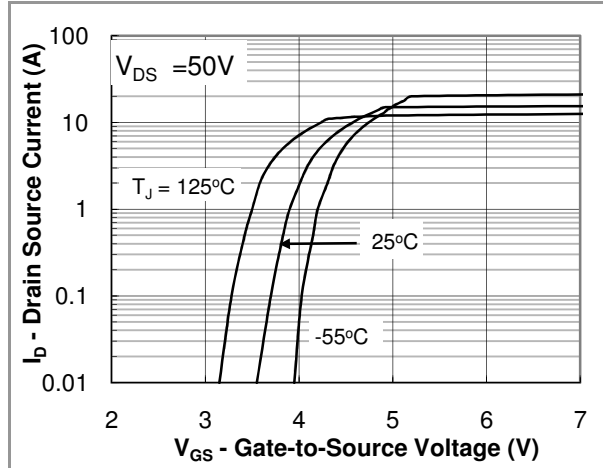


Fig.2 Transfer Characteristic

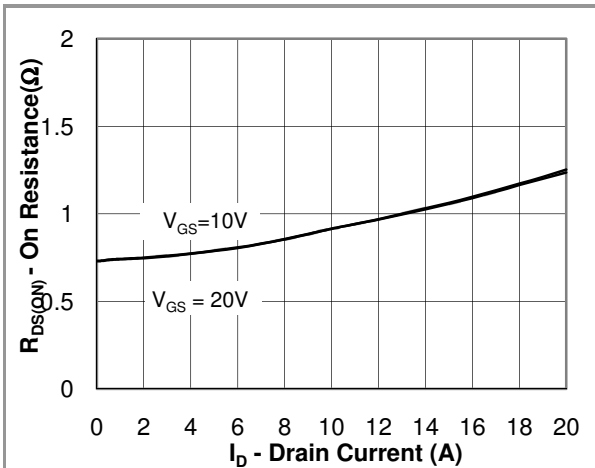


Fig.3 On Resistance vs Drain Current

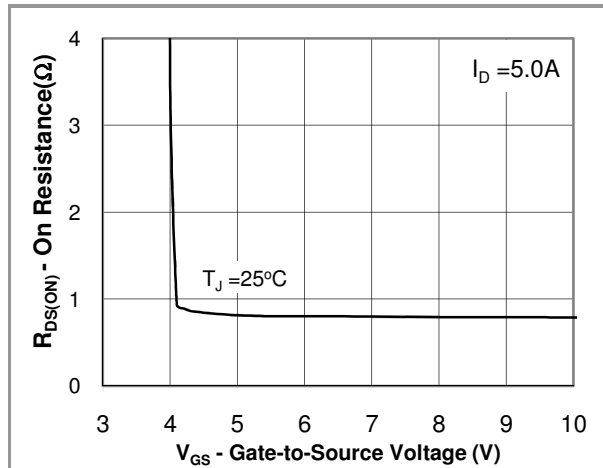


Fig.4 On Resistance vs Gate to Source Voltage

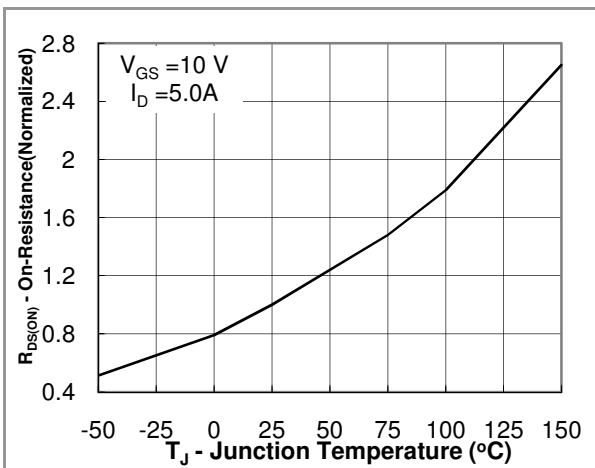


Fig.5 On Resistance vs Junction Temperature

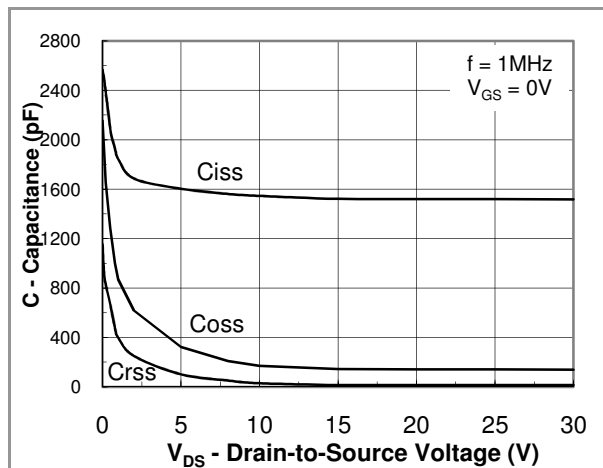
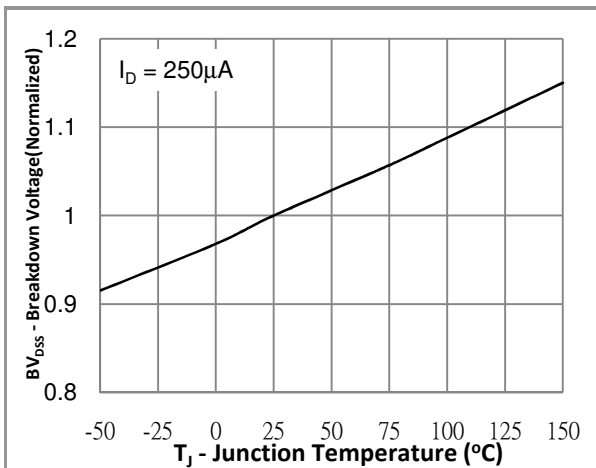
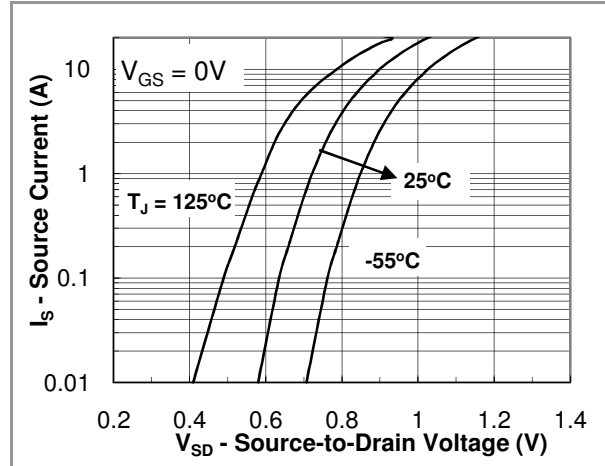
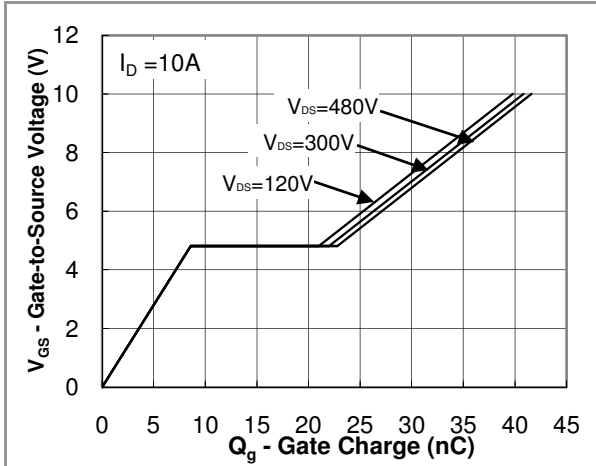


Fig.6 Capacitance



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